

Silicon NPN Power Transistors

2SD1911

DESCRIPTION

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- With TO-3PFM package
- High breakdown voltage
- High speed switching
- Built-in damper diode

APPLICATIONS

- For use in TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

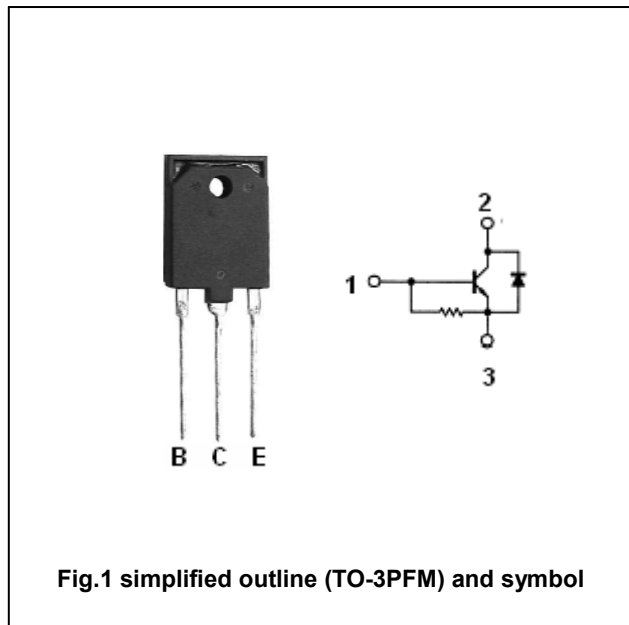


Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1\text{A}$; $I_B=0$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=4.5\text{A}$; $I_B=1.2\text{A}$			5.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=4.5\text{A}$; $I_B=1.2\text{A}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800\text{V}$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6\text{V}$; $I_C=0$	50		200	mA
h_{FE}	DC current gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$	8		25	
V_F	Diode forward voltage	$I_F=5\text{A}$			2.0	V

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PACKAGE OUTLINE

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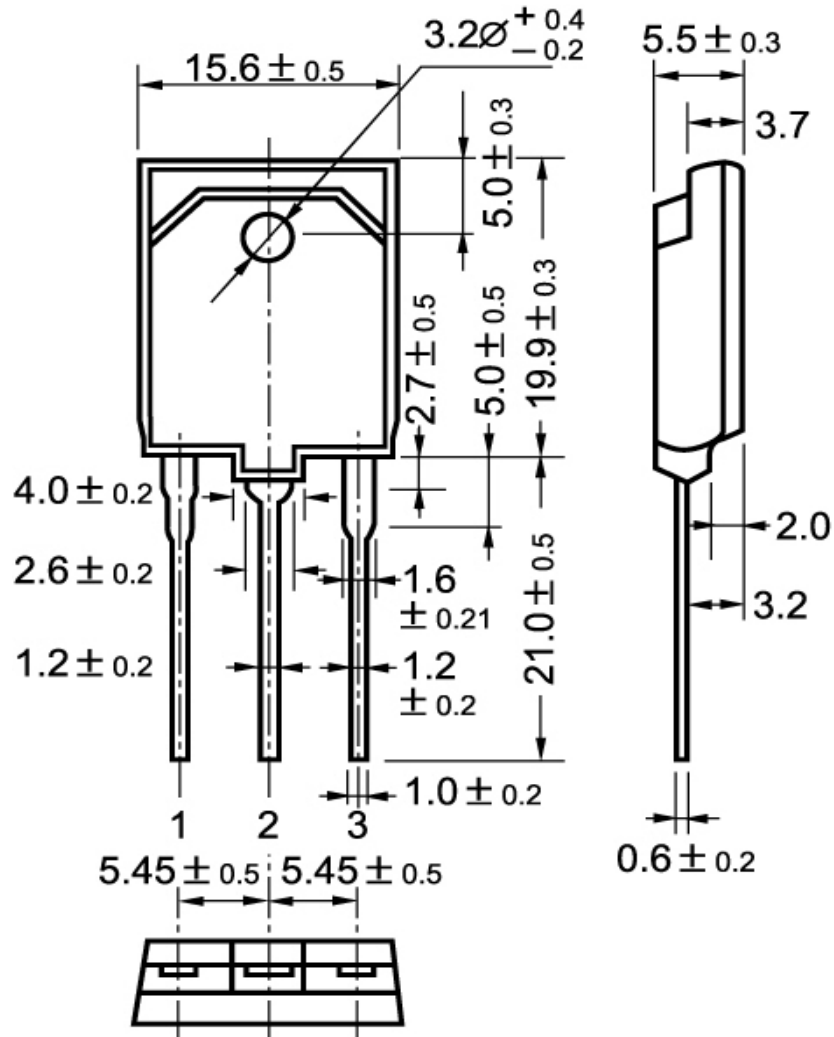


Fig.2 outline dimensions